# RENESAS

# ISL28233, ISL28433

Dual and Quad Micropower Chopper Stabilized, RRIO Operational Amplifiers

The <u>ISL28233</u> and <u>ISL28433</u> are dual and quad micropower, chopper stabilized operational amplifiers that are optimized for single and dual supply operation from 1.8V to 6.0V and  $\pm 0.825V$  to  $\pm 3.0V$ . Their low supply current of 18µA and wide input range enable the ISL28233, ISL28433 to be excellent general purpose op amps for a wide range of applications. The ISL28233 and ISL28433 are ideal for handheld devices that operate off 2 AA or single Li-ion batteries.

The ISL28233 is available in 8 Ld MSOP, 8 Ld SOIC and 8 Ld DFN packages. The ISL28433 is available in 14 Ld TSSOP and 14 Ld SOIC packages. All devices operate over the temperature range of -40°C to +125°C.

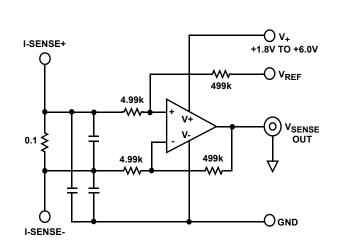
# **Features**

•	Low Input Offset Voltage	6µV, Max.
•	Low Offset Drift 0.0	5µV/°C, Max.
•	Quiescent Current (Per Amplifier)	<b>18µA</b> , Typ.

- Single Supply Range .....+1.8V to +6.0V
- Dual Supply Range ..... ±0.825V to ±3.0V
- Low Noise (0.01Hz to 10Hz) .....1.0μV<sub>P-P</sub>, Typ.
- Rail-to-Rail Inputs and Output
- Operating Temperature Range .....-40°C to +125°C

## **Applications**

- Bi-Directional Current Sense
- Temperature Measurement
- Medical Equipment
- Electronic Weigh Scales
- Precision/Strain Gauge Sensor
- Precision Regulation
- Low Ohmic Current Sense
- High Gain Analog Front Ends



**BI-DIRECTIONAL CURRENT SENSE AMPLIFIER** 



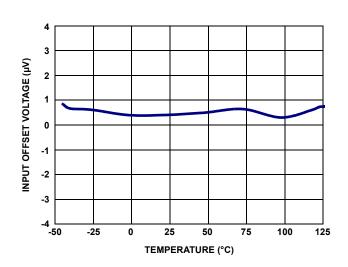


FIGURE 2. V<sub>OS</sub> vs TEMPERATURE



# **Ordering Information**

PART NUMBER (Notes 2, 3)	PART MARKING	PACKAGE DESCRIPTION (RoHS Compliant)	PKG. DWG. #	CARRIER TYPE (Note 1)	TEMP RANGE			
ISL28233FUZ	233FZ	8 Ld MSOP	<u>M8.118A</u>	Tube	-40°C to +125°C			
ISL28233FUZ-T7				Reel, 1.5k	-			
ISL28233FUZ-T7A				Reel, 250				
ISL28233FRZ	233Z	8 Ld 3mmx3mm DFN	<u>L8.3x3J</u>	Tube				
ISL28233FRZ-T7			-		Reel, 1k			
ISL28233FRZ-T13				Reel, 2.5k				
ISL28233FBZ	28233	8 Ld SOIC	<u>M8.15E</u>	<u>M8.15E</u> T	Tube			
ISL28233FBZ-T7	FBZ			Reel, 1k	-			
ISL28233FBZ-T7A				Reel, 250				
ISL28433FBZ	28433	14 Ld SOIC	<u>MDP0027</u>	Tube	_			
ISL28433FBZ-T7	FBZ		BZ		Reel, 1k	-		
ISL28433FBZ-T7A				Reel, 250	-			
ISL28433FVZ	28433	14 Ld TSSOP	MDP0044	Tube	_			
ISL28433FVZ-T13	FVZ			Reel, 2.5k	-			
ISL28233SOICEVAL1Z	ISL28233 Evaluation	Board		1				
ISL28433TSSOPEVAL1Z	ISL28433 Evaluation	ISL28433 Evaluation Board TSSOP package						
ISL28433SOICEVAL1Z	ISL28433 Evaluation Board SOIC package							

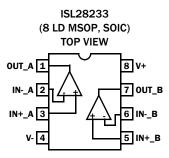
NOTES:

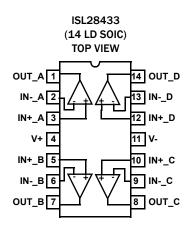
1. Refer to TB347 for details on reel specifications.

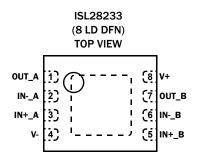
 These Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

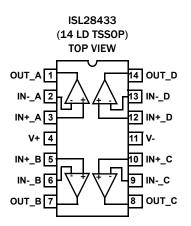
3. For Moisture Sensitivity Level (MSL), please see device information page for <u>ISL28233</u>, <u>ISL28433</u>. For more information on MSL please see techbrief <u>TB363</u>.

# **Pin Configurations**









# **Pin Descriptions**

ISL28233 (8 LD MSOP, SOIC, DFN)	ISL28433 (14 LD TSSOP, SOIC)	PIN NAME	FUNCTION	EQUIVALENT CIRCUIT
3	3	IN+_A	Non-inverting input	N
5	5	IN+_B		
-	10	IN+_C		
-	12	IN+_D		IN- CLOCK GEN + DRIVERS Circuit 1
4	11	V-	Negative supply	
2	2	INA	Inverting input	(See Circuit 1)
6	6	INB		
-	9	INC		
-	13	IND		
1	1	OUT_A	Output	V+
7	7	OUT_B		····
-	8	OUT_C		
-	14	OUT_D		t t t t t t t t t t t t t t t t t
8	4	V+	Positive supply	
-	-	PAD	Thermal Pad	Thermal Pad. Connect to most negative supply. DFN package only.



### **Absolute Maximum Ratings**

Max Sup	ply Voltage V+ to V	6.5V
Max Volt	age VIN to GND	(V0.3V) to (V++0.3V)V
Max Inpu	ut Differential Voltage	6.5V
Max Inpu	ut Current	20mA
Max Volt	age VOUT to GND (10s)	±3.0V
ESD Tole	erance	
Huma	n Body Model (Tested per JESD22-A11	4F)4000V
Machi	ne Model (Tested per JESD22-A115B)	
Charg	ed Device Model (Tested per JESD22-C	110D) 2000V
Latch-Up	(Tested per JESD78B)	+125°C

### **Thermal Information**

Thermal Resistance (Typical)	$\theta_{\text{JA}}(^{\circ}\text{C}/\text{W})$	θ <sub>JC</sub> (°C/W)
14 Ld TSSOP (Notes 4, 7)	110	40
14 Ld SOIC (Notes 4, 7)	75	47
8 Ld MSOP (Notes 4, 7)	180	65
8 Ld SOIC (Notes 4, 7)	125	90
8 Ld DFN (Notes 5, 6)	53	12
Maximum Storage Temperature Range	· · · · · · · · · · · - <del>(</del>	65°C to +150°C
Pb-Free Reflow Profile		see <u>TB493</u>

### **Operating Conditions**

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

#### NOTES:

4.  $\theta_{JA}$  is measured with the component mounted on a high effective thermal conductivity test board in free air. See <u>TB379</u> for details.

- 5.  $\theta_{JA}$  is measured in free air with the component mounted on a high effective thermal conductivity test board with "direct attach" features. See TB379.
- 6. For  $\theta_{JC}$ , the "case temp" location is the center of the exposed metal pad on the package underside.

7. For  $\theta_{\text{JC}},$  the "case temp" location is taken at the package top center.

**Electrical Specifications** V + = 5V, V - = 0V,  $V_{CM} = 2.5V$ ,  $T_A = +25$ °C,  $R_L = 10k\Omega$ , unless otherwise specified. Boldface limits apply over the operating temperature range, 40°C to +125°C.

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 8)	түр	MAX (Note 8)	UNIT
C SPECIFICATIO	NS					
V <sub>OS</sub>	Input Offset Voltage		-6	±2	6	μV
		T = -40°C to +125°C	-11	-	11	μV
TCV <sub>OS</sub>	Input Offset Voltage Temperature Coefficient	T = -40°C to +125°C	-0.05	0.01	0.05	µV∕°C
los	Input Offset Current		-	10	-	pА
TCI <sub>OS</sub>	Input Offset Current Temperature Coefficient	T = -40 °C to +85 °C	-	0.11	-	pA/°0
Ι <sub>Β</sub>	Input Bias Current	T = -40 °C to +85 °C	-180	-	180	pА
		T = -40°C to +125°C	-600	-	600	pА
TCIB	Input Bias Current Temperature Coefficient	T = -40 °C to +85 °C	-	0.49	-	pA/°
CMIR		V+ = 5.0V, V- = 0V Guaranteed by CMRR	-0.1	-	5.1	v
CMRR	Common Mode Rejection Ratio	VCM = -0.1V to 5.1V	118	125	-	dB
			115	-	-	dB
PSRR	Power Supply Rejection Ratio	Vs = 1.8V to 6.0V	110	138	-	dB
			110	-	-	dB
V <sub>OH</sub>	Output Voltage, High		4.965	4.981	-	v
V <sub>OL</sub>	Output Voltage, Low		-	18	35	mV
A <sub>OL</sub>	Open Loop Gain	$R_L = 1M\Omega$	-	174	-	dB
V+	Supply Voltage	Guaranteed by PSRR	1.8	-	6.0	v
۱ <sub>S</sub>	Supply Current, Per Amplifier	R <sub>L</sub> = OPEN	-	18	25	μA
			-	-	35	μA
I <sub>SC+</sub>	Output Source Short Circuit Current	R <sub>L</sub> = Short to V-	13	17	26	mA
I <sub>SC-</sub>	Output Sink Short Circuit Current	R <sub>L</sub> = Short to V+	-26	-19	-13	mA



<b>Electrical Specifications</b> V+ = 5V, V- = 0V, V <sub>CM</sub> = 2.5V, T <sub>A</sub> = +25°C, R <sub>L</sub> = $10k\Omega$ , unless otherwise specified. Boldface limits apply over
the operating temperature range,-40°C to +125°C. (Continued)

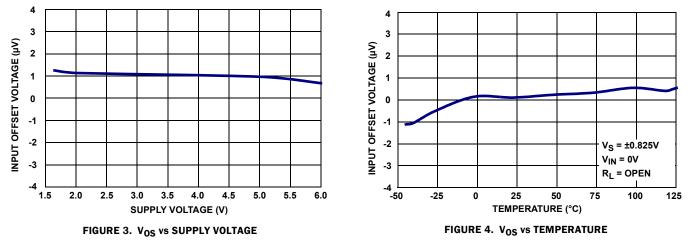
PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 8)	ТҮР	MAX (Note 8)	UNIT
AC SPECIFICATION	IS		1			
GBWP	Gain Bandwidth Product	$\label{eq:relation} \begin{split} \textbf{A}_{V} &= \textbf{100},  \textbf{R}_{F} = \textbf{100} \textbf{k} \Omega,  \textbf{R}_{G} = \textbf{1} \textbf{k} \Omega, \\ \textbf{R}_{L} &= \textbf{10} \textbf{k} \Omega \text{ to } \textbf{V}_{CM} \end{split}$	-	400	-	kHz
e <sub>N</sub> V <sub>P-P</sub>	Peak-to-Peak Input Noise Voltage	f = 0.01Hz to 10Hz	-	1.0	-	μV <sub>P-P</sub>
e <sub>N</sub>	Input Noise Voltage Density	f = 1kHz	-	65	-	nV/√(Hz
i <sub>N</sub>	Input Noise Current Density	f = 1kHz	-	72	-	fA/√(Hz)
		f = 10Hz	-	79	-	fA/√(Hz)
C <sub>in</sub>	Differential Input Capacitance	f = 1MHz	-	1.6	-	pF
	Common Mode Input Capacitance		-	1.12	-	pF
<b>FRANSIENT RESPO</b>	DNSE		1			
SR	Positive Slew Rate	$V_{OUT}$ = 1V to 4V, R <sub>L</sub> = 10kΩ	-	0.2	-	V/µs
	Negative Slew Rate	-	-	0.1	-	V/µs
t <sub>r</sub> , t <sub>f</sub> , Small Signal	Rise Time, t <sub>r</sub> 10% to 90%	$\textbf{A}_{\textbf{V}} = \textbf{+1},  \textbf{V}_{\textbf{OUT}} = \textbf{0.1} \textbf{V}_{\textbf{P-P}},  \textbf{R}_{\textbf{F}} = \textbf{0} \boldsymbol{\Omega},$	-	1.1	-	μs
	Fall Time, t <sub>f</sub> 10% to 90%	R <sub>L</sub> = 10kΩ, C <sub>L</sub> = 1.2pF	-	1.1	-	μs
t <sub>r</sub> , t <sub>f</sub> Large Signal	Rise Time, t <sub>r</sub> 10% to 90%	$A_V = +1, V_{OUT} = 2V_{P-P}, R_F = 0\Omega,$	-	20	-	μs
	Fall Time, t <sub>f</sub> 10% to 90%	$R_{L} = 10k\Omega, C_{L} = 1.2pF$	-	30	-	μs
t <sub>s</sub>	Settling Time to 0.1%, 2V <sub>P-P</sub> Step	$\textbf{A}_{\textbf{V}} = \textbf{+1}, \textbf{R}_{\textbf{F}} = \textbf{0}\Omega, \textbf{R}_{\textbf{L}} = \textbf{10}\textbf{k}\Omega, \textbf{C}_{\textbf{L}} = \textbf{1.2}\textbf{p}\textbf{F}$	-	35	-	μs
t <sub>recover</sub>	Output Overload Recovery Time, Recovery to 90% of output saturation	$A_V = +2, R_F = 10 k\Omega, R_L = 0 pen, C_L = 3.7 pF$	-	10.5	-	μs

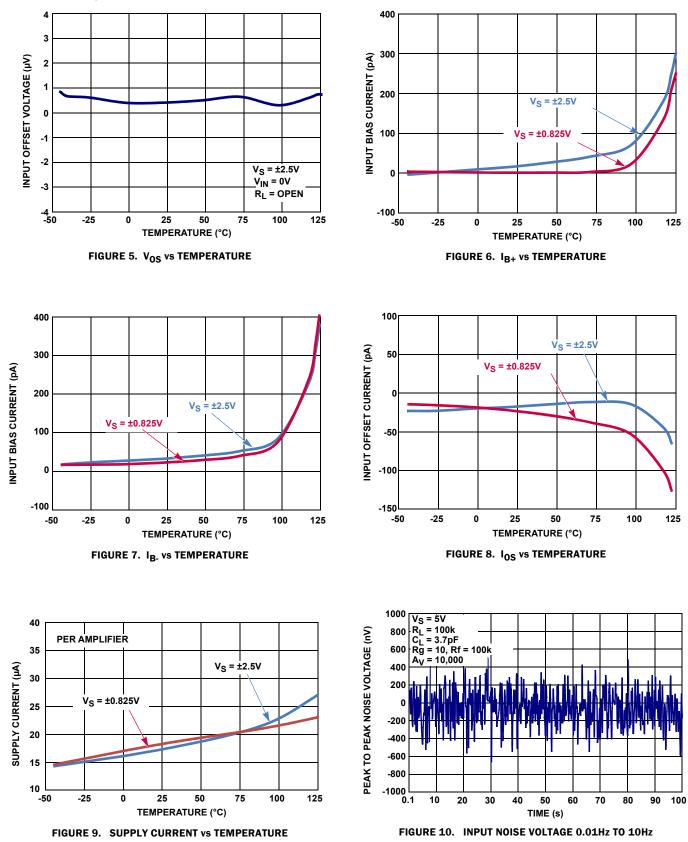
NOTE:

8. Compliance to datasheet limits is assured by one or more methods: production test, characterization and/or design.

# **Typical Performance Curves**

V+ = 5V, V- = 0V, V\_{CM} = 2.5V, R<sub>L</sub> = Open, T = +25  $^{\circ}$  C, unless otherwise specified.





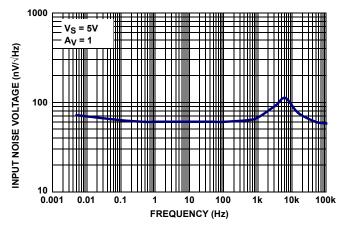


FIGURE 11. INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

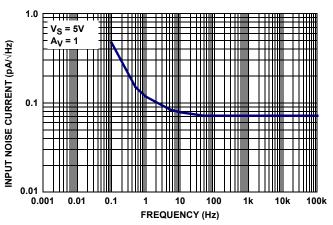
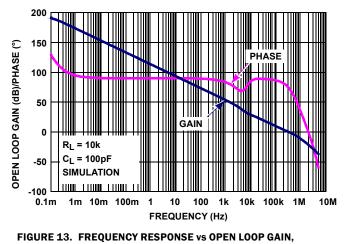


FIGURE 12. INPUT NOISE CURRENT DENSITY vs FREQUENCY



 $R_L = 10k\Omega$ 

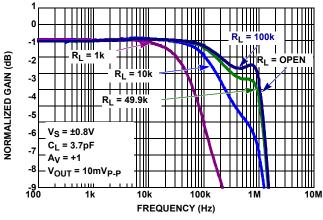
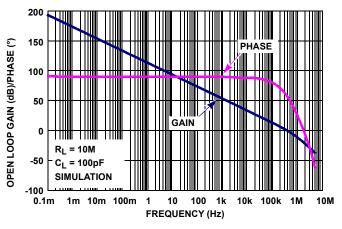


FIGURE 15. GAIN vs FREQUENCY vs  $R_L$ ,  $V_S = \pm 0.8V$ 





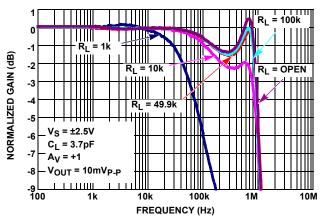


FIGURE 16. GAIN vs FREQUENCY vs RL, VS = ±2.5V



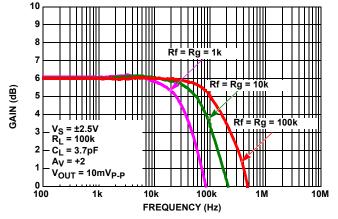


FIGURE 17. GAIN vs FREQUENCY vs FEEDBACK RESISTOR VALUES  $$R_{f}/R_{g}$$ 

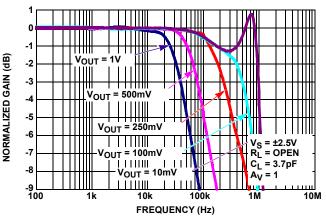


FIGURE 18. GAIN vs FREQUENCY vs V<sub>OUT</sub>, R<sub>L</sub> = OPEN

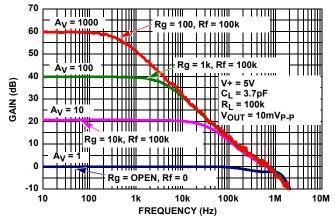


FIGURE 19. FREQUENCY RESPONSE vs CLOSED LOOP GAIN

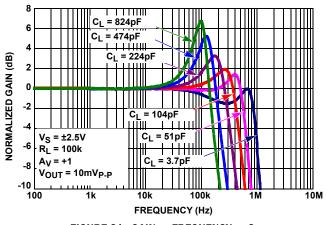


FIGURE 21. GAIN vs FREQUENCY vs CL

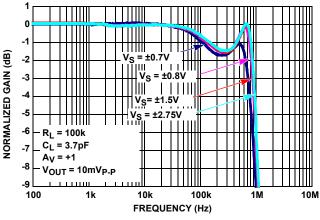
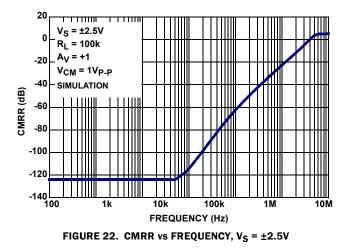
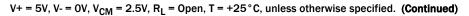


FIGURE 20. GAIN vs FREQUENCY vs SUPPLY VOLTAGE







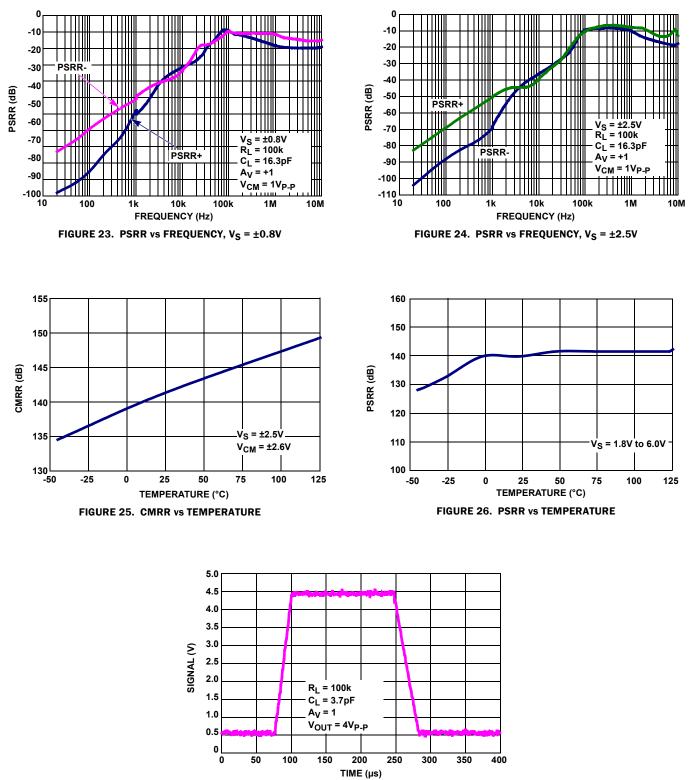
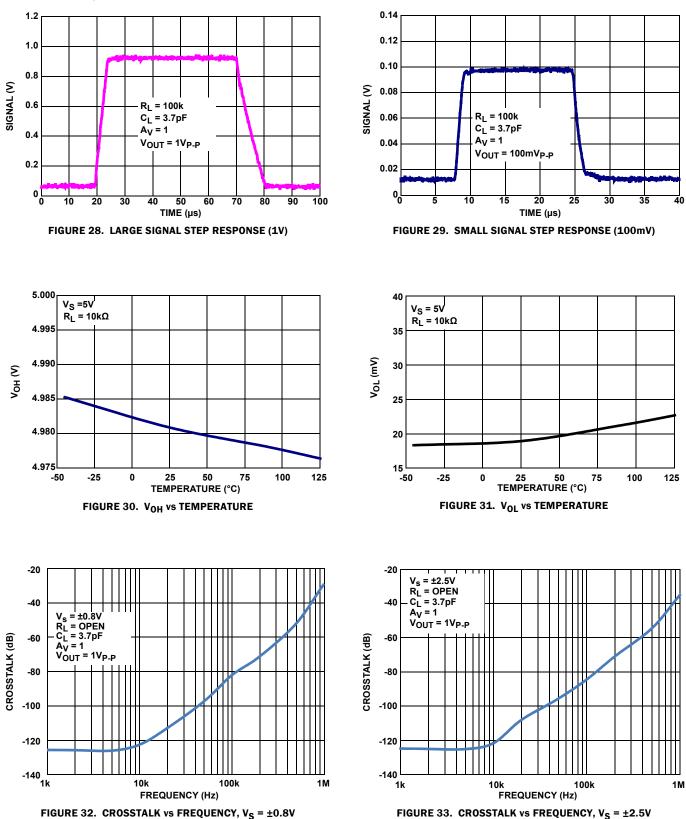
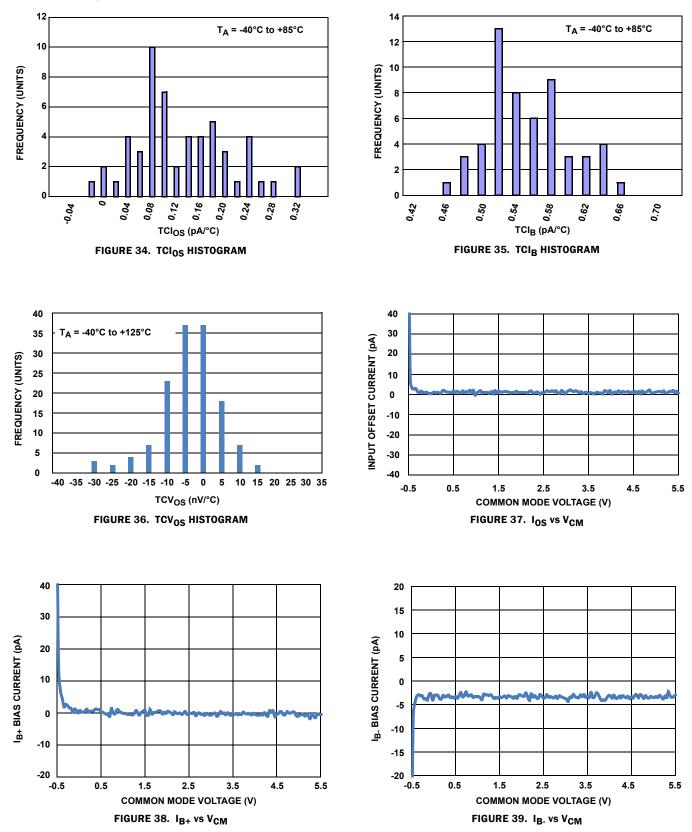


FIGURE 27. LARGE SIGNAL STEP RESPONSE (4V)

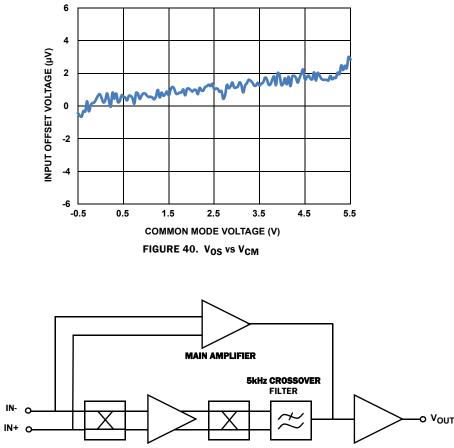








RENESAS



CHOPPER STABILIZED DC OFFSET CORRECTION



# **Applications Information**

### **Functional Description**

The ISL28233 and ISL28433 use a proprietary chopper-stabilized technique (see Figure 41) that combines a 400kHz main amplifier with a very high open loop gain (174dB) chopper amplifier to achieve very low offset voltage and drift (2 $\mu$ V, 0.01 $\mu$ V/°C typical) while consuming only 18 $\mu$ A of supply current per channel.

This multi-path amplifier architecture contains a time continuous main amplifier whose input DC offset is corrected by a parallelconnected, high gain chopper stabilized DC correction amplifier operating at 100kHz. From DC to ~5kHz, both amplifiers are active with DC offset correction and most of the low frequency gain is provided by the chopper amplifier. A 5kHz crossover filter cuts off the low frequency amplifier path leaving the main amplifier active out to the 400kHz gain-bandwidth product of the device.

The key benefits of this architecture for precision applications are very high open loop gain, very low DC offset, and low 1/f noise. The noise is virtually flat across the frequency range from a few millihertz out to 100kHz, except for the narrow noise peak at the amplifier crossover frequency (5kHz).

### **Rail-to-rail Input and Output (RRIO)**

The RRIO CMOS amplifier uses parallel input PMOS and NMOS that enable the inputs to swing 100mV beyond either supply rail. The inverting and non-inverting inputs do not have back-to-back input clamp diodes and are capable of maintaining high input impedance at high differential input voltages. This is effective in eliminating output distortion caused by high slew-rate input signals.

The output stage uses common source connected PMOS and NMOS devices to achieve rail-to-rail output drive capability with 17mA current limit and the capability to swing to within 20mV of either rail while driving a  $10k\Omega$  load.



### **IN+ and IN- Protection**

All input terminals have internal ESD protection diodes to both positive and negative supply rails, limiting the input voltage to within one diode beyond the supply rails. For applications where either input is expected to exceed the rails by 0.5V, an external series resistor must be used to ensure the input currents never exceed 20mA (see Figure 42).

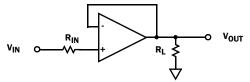


FIGURE 42. INPUT CURRENT LIMITING

### Layout Guidelines for High Impedance Inputs

To achieve the maximum performance of the high input impedance and low offset voltage of the ISL28233 and ISL28433 amplifiers, care should be taken in the circuit board layout. The PC board surface must remain clean and free of moisture to avoid leakage currents between adjacent traces. Surface coating of the circuit board will reduce surface moisture and provide a humidity barrier, reducing parasitic resistance on the board.

### **High Gain, Precision DC-Coupled Amplifier**

The circuit in Figure 43 implements a single-stage DC-coupled amplifier with an input DC sensitivity of under 100nV that is only possible using a low VOS amplifier with high open loop gain. High gain DC amplifiers operating from low voltage supplies are not practical using typical low offset precision op amps. For example, a typical precision amplifier in a gain of 10kV/V with a  $\pm$ 100µV V<sub>OS</sub> and offset drift 0.5µV/°C of a low offset op amp would produce a DC error of >1V with an additional 5mV/°C of temperature dependent error making it difficult to resolve DC input voltage changes in the mV range.

The  $\pm 6\mu V \max V_{OS}$  and  $0.05\mu V/^{\circ}C$  max temperature drift of the ISL28233, ISL28433 produces a temperature stable maximum DC output error of only  $\pm 60mV$  with a maximum output temperature drift of  $0.5mV/^{\circ}C$ . The additional benefit of a very low 1/f noise corner frequency and some feedback filtering enables DC voltages and voltage fluctuations well below 100nV to be easily detected with a simple single stage amplifier.

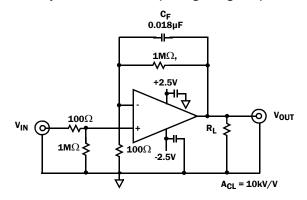


FIGURE 43. HIGH GAIN, PRECISION DC-COUPLED AMPLIFIER

### ISL28233, ISL28433 SPICE Model

Figure 44 shows the SPICE model schematic and Figure 45 shows the net list for the ISL28233, ISL28433 SPICE model. The model is a simplified version of the actual device and simulates important parameters such as noise, Slew Rate, Gain and Phase. The model uses typical parameters from the "Electrical Specifications Table" on page 5. The poles and zeroes in the model were determined from the actual open and closed-loop gain and phase response. This enables the model to present an accurate AC representation of the actual device. The model is configured for ambient temperature of +25°C.

Figures 46 through 53 show the characterization vs simulation results for the Noise Density, Frequency Response vs Close Loop Gain, Gain vs Frequency vs C<sub>1</sub> and Large Signal Step Response (4V).

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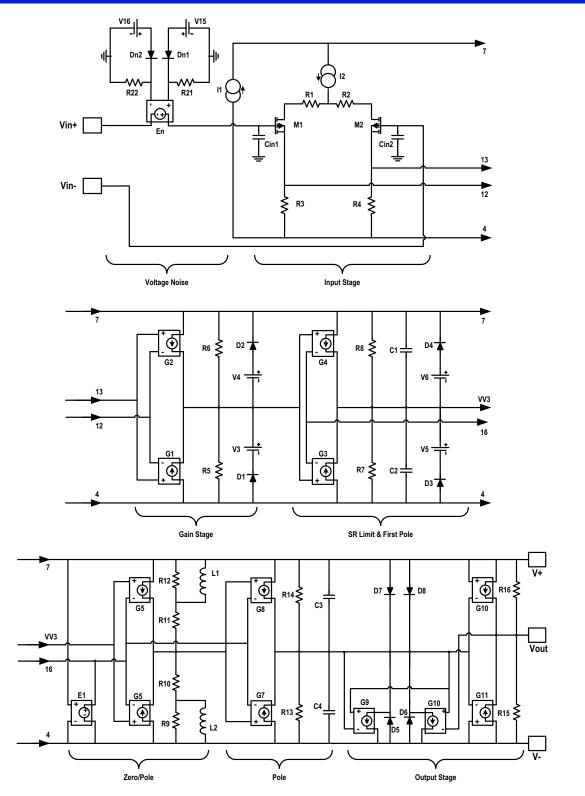


FIGURE 44. SPICE CIRCUIT SCHEMATIC



* Revisior * AC char *Copyright *Refer to d *this mode		)9 /oltag esas C ENSE ir acce	e Noise orporat STATE ptance cense S	e ion MENT with th tateme ut	e ent. supply	of upply output   6
* *Voltage I	Voise					
	102 101 104 103 0 101 12 0 103 12 8 3 101 10 102 0 0.1 104 0 0.1	DN :0k :0k 03 1 Vdc				
C_Cin2 R_R1 R_R2 R_R3	80 0.4p		isil			
M_M2 + L=50u + W=50u	13 2 11 1′	1 pmo	sisil			
I_I1 4	4 7 DC 92uA 7 10 DC 100					
*Gain stag G_G1 G_G2 R_R5 R_R6 D_D1 D_D2 V_V3 V_V4 *	ge 4 VV2 13 7 VV2 13 4 VV2 1.3 VV2 7 1.3 4 14 DX 15 7 DX VV2 14 0.7 15 VV2 0.7	12 0.0 Meg Meg 'Vdc				
*SR limit 1 G_G3 G_G4 R_R7 R_R8	irst pole 4 VV3 VV 7 VV3 VV 4 VV3 1m VV3 7 1m	′2 16 <sup>·</sup> eg				

C_C2 D_D3 D_D4 V_V5 V_V6 *	4 VV3 12u 4 17 DX 18 7 DX VV3 17 0.7Vdc 18 VV3 0.7Vdc
*Zero/Pol- E_E1 G_G5 G_G6 L_L1 R_R12 R_R11 L_L2 R_R9 R_R10 *Pole G_G7 G_G8 C_C3 C_C4 R_R13 R_R14	e 16 4 7 4 0.5 4 VV4 VV3 16 0.000001 7 VV4 VV3 16 0.000001 20 7 0.3H 20 7 2.5meg VV4 20 1meg 4 19 0.3H 4 19 2.5meg 19 VV4 1meg 4 VV5 VV4 16 0.000001 7 VV5 VV4 16 0.000001 VV5 7 0.12p 4 VV5 0.12p 4 VV5 1meg VV5 7 1meg
*	t to t inneg
*Output S G_G9 G_G10 D_D5 D_D6 D_D7 D_D8 R_R15 R_R16 G_G11 G_G12	21 4 6 VV5 0.0000125 22 4 VV5 6 0.0000125 4 21 DY 4 22 DY 7 21 DX 7 22 DX 4 6 8k 6 7 8k

.model pmosisil pmos (kp=16e-3 vto=10m) .model DN D(KF=6.4E-16 AF=1) .MODEL DX D(IS=1E-18 Rs=1) .MODEL DY D(IS=1E-15 BV=50 Rs=1) .ends ISL28233

FIGURE 45. SPICE NET LIST

VV3 7 12u

C\_C1



# **Characterization vs Simulation Results**

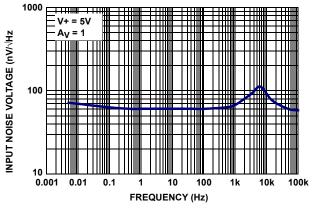


FIGURE 46. CHARACTERIZED INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

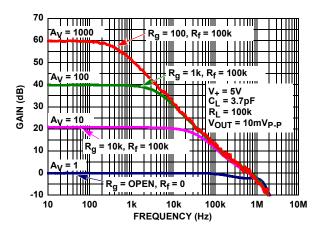


FIGURE 48. CHARACTERIZED FREQUENCY RESPONSE vs CLOSED LOOP GAIN

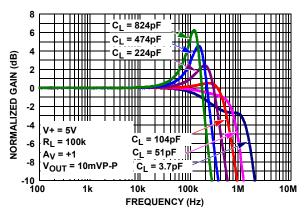


FIGURE 50. CHARACTERIZED GAIN vs FREQUENCY vs CL

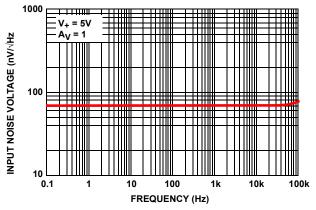


FIGURE 47. SIMULATED INPUT NOISE VOLTAGE DENSITY vs FREQUENCY

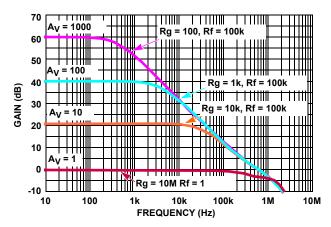


FIGURE 49. SIMULATED FREQUENCY RESPONSE vs CLOSED LOOP GAIN

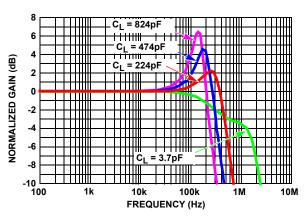
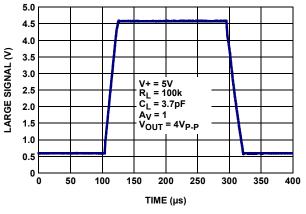


FIGURE 51. SIMULATED GAIN vs FREQUENCY vs CL

# Characterization vs Simulation Results (Continued)





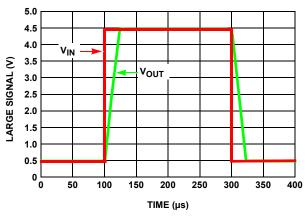


FIGURE 53. SIMULATED LARGE SIGNAL STEP RESPONSE (4V)

# **Revision History**

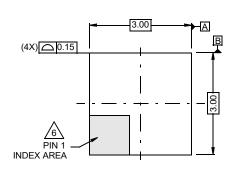
The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to web to make sure you have the latest Rev.

DATE	REVISION	CHANGE
Apr 15, 2024	3.01	Removed Related Literature section. Updated Ordering Information table. Removed TDFN information from document. Removed Products section. Updated POD L8.3X3J to the latest revision; changes are as follows: -Tiebar Note 5 updated.
May 31, 2011	3.00	Changed minimum operating supply voltage from +1.65V to +1.8V throughout entire datasheet.
Mar 24, 2011		Added to Ordering Information Table on page 2 - ISL28233SOICEVAL1Z, ISL28433TSSOPEVAL1Z, ISL28433SOICEVAL1Z
Dec 2, 2010	2.00	<ul> <li>Added "Related Literature" on page 1</li> <li>Removed "Coming Soon" from ISL28233FRZ device (8 Ld DFN) in "Ordering Information" on page 2.</li> <li>Corrected Thermal Pad Pin Name in "Pin Descriptions" on page 4 from "NC" to "PAD"</li> <li>Corrected θ<sub>JA</sub> note for TDFN package in "Thermal Information" on page 5 from "θ<sub>JA</sub> is measured with the component mounted on a high effective thermal conductivity test board in free air. See Tech Brief TB379 for details." To "θ<sub>JA</sub> is measured in free air with the component mounted on a high effective thermal conductivity test board on a high effective thermal conductivity test board on a high effective thermal conductivity test board with "direct attach" features. See Tech Brief TB379." (since TDFN has thermal pad; TDFN package option not released yet)</li> </ul>
Oct 27, 2010	1.00	Changed Part Marking for ISL28233FUZ from 8233Z to 233FZ in "Ordering Information" table on page 2 Added ISL28233 in DFN package to Ordering Information" table on page 2. On page 6, removed Note 8. Changed note in MIN MAX columns of "Electrical Specifications" table from: "Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested." To: "Compliance to datasheet limits is assured by one or more methods: production test, characterization and/or design."
Aug 25, 2010	0.00	Initial Release.

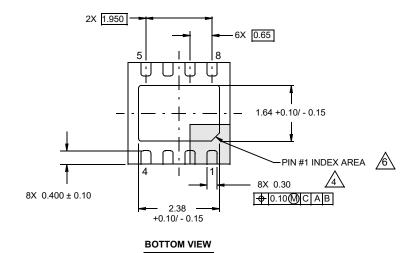
# **Package Outline Drawings**

For the most recent package outline drawing, see L8.3x3J.

L8.3x3J 8 LEAD DUAL FLAT NO-LEAD PLASTIC PACKAGE Rev 1 3/15

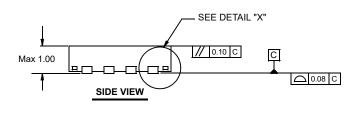


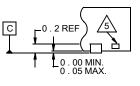
TOP VIEW



(2.80) (2.80) (2.80) (1.64)(1.6

TYPICAL RECOMMENDED LAND PATTERN







#### NOTES:

- Dimensions are in millimeters. Dimensions in ( ) for Reference Only.
- 2. Dimensioning and tolerancing conform to AMSE Y14.5m-1994.
- 3. Unless otherwise specified, tolerance : Decimal  $\pm 0.05$

Dimension applies to the metallized terminal and is measured between 0.15mm and 0.30mm from the terminal tip.

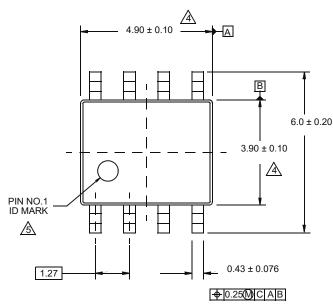
- <u>Z</u>. Tiebar shown (if present) is a non-functional feature and may be located on any of the 4 sides (or ends).
- Ch. The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.



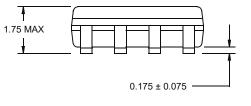
For the most recent package outline drawing, see M8.15E.

#### M8.15E

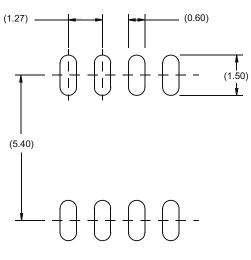
8 LEAD NARROW BODY SMALL OUTLINE PLASTIC PACKAGE Rev 0, 08/09



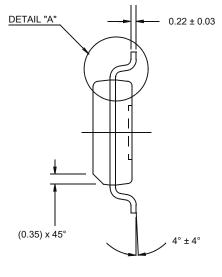
TOP VIEW



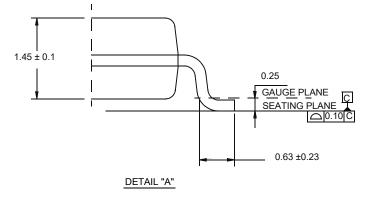
SIDE VIEW "A



TYPICAL RECOMMENDED LAND PATTERN



SIDE VIEW "B"



#### NOTES:

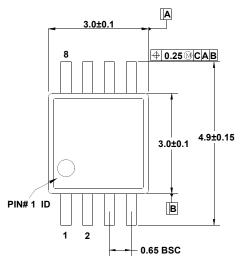
- Dimensions are in millimeters.
   Dimensions in ( ) for Reference Only.
- 2. Dimensioning and tolerancing conform to AMSE Y14.5m-1994.
- 3. Unless otherwise specified, tolerance : Decimal  $\pm 0.05$
- 4. Dimension does not include interlead flash or protrusions. Interlead flash or protrusions shall not exceed 0.25mm per side.
- 5. The pin #1 identifier may be either a mold or mark feature.
- 6. Reference to JEDEC MS-012.

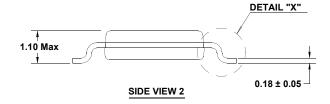


#### For the most recent package outline drawing, see <u>M8.118A</u>.

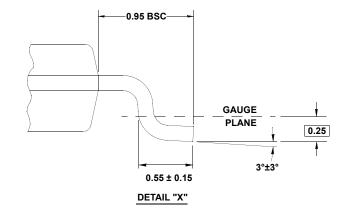
#### M8.118A

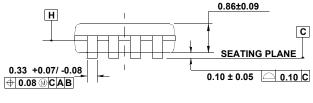
8 LEAD MINI SMALL OUTLINE PLASTIC PACKAGE (MSOP) Rev 0, 9/09



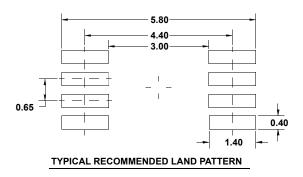


TOP VIEW





SIDE VIEW 1

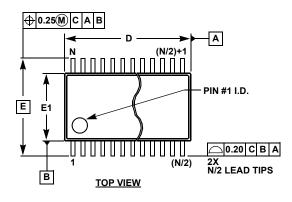


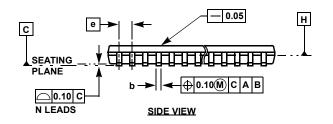
#### NOTES:

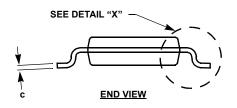
- 1. Dimensions are in millimeters.
- 2. Dimensioning and tolerancing conform to JEDEC MO-187-AA and AMSE Y14.5m-1994.
- 3. Plastic or metal protrusions of 0.15mm max per side are not included.
- 4. Plastic interlead protrusions of 0.25mm max per side are not included.
- 5. Dimensions "D" and "E1" are measured at Datum Plane "H".
- 6. This replaces existing drawing # MDP0043 MSOP 8L.

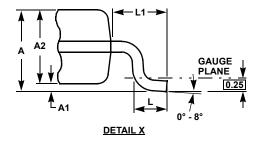


For the most recent package outline drawing, see MDP0044.









### **MDP0044**

THIN SHRINK SMALL OUTLINE PACKAGE FAMILY

	MILLIMETERS								
SYMBOL	14 LD	16 LD	20 LD	24 LD	28 LD	TOLERANCE			
А	1.20	1.20	1.20	1.20	1.20	Max			
A1	0.10	0.10	0.10	0.10	0.10	±0.05			
A2	0.90	0.90	0.90	0.90	0.90	±0.05			
b	0.25	0.25	0.25	0.25	0.25	+0.05/-0.06			
С	0.15	0.15	0.15	0.15	0.15	+0.05/-0.06			
D	5.00	5.00	6.50	7.80	9.70	±0.10			
E	6.40	6.40	6.40	6.40	6.40	Basic			
E1	4.40	4.40	4.40	4.40	4.40	±0.10			
е	0.65	0.65	0.65	0.65	0.65	Basic			
L	0.60	0.60	0.60	0.60	0.60	±0.15			
L1	1.00	1.00	1.00	1.00	1.00	Reference			
	Rev. F 2/07								

#### NOTES:

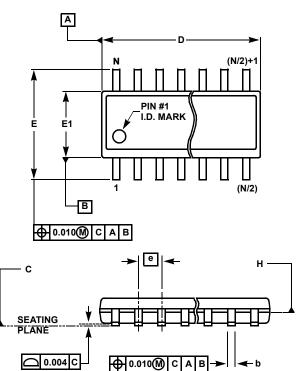
 Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15mm per side.

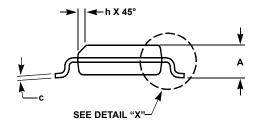
 Dimension "E1" does not include interlead flash or protrusions. Interlead flash and protrusions shall not exceed 0.25mm per side.

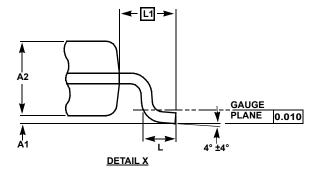
11. Dimensions "D" and "E1" are measured at dAtum Plane H.

12. Dimensioning and tolerancing per ASME Y14.5M-1994.

For the most recent package outline drawing, see MDP0027.







### MDP0027

SMALL OUTLINE PACKAGE FAMILY (SO)

SYMBOL	INCHES								
	SO-8	SO-14	SO16 (0.150")	SO16 (0.300") (SOL-16)	SO20 (SOL-20)	SO24 (SOL-24)	SO28 (SOL-28)	TOLERANCE	NOTES
А	0.068	0.068	0.068	0.104	0.104	0.104	0.104	MAX	-
A1	0.006	0.006	0.006	0.007	0.007	0.007	0.007	±0.003	-
A2	0.057	0.057	0.057	0.092	0.092	0.092	0.092	±0.002	-
b	0.017	0.017	0.017	0.017	0.017	0.017	0.017	±0.003	-
С	0.009	0.009	0.009	0.011	0.011	0.011	0.011	±0.001	-
D	0.193	0.341	0.390	0.406	0.504	0.606	0.704	±0.004	1, 3
Е	0.236	0.236	0.236	0.406	0.406	0.406	0.406	±0.008	-
E1	0.154	0.154	0.154	0.295	0.295	0.295	0.295	±0.004	2, 3
е	0.050	0.050	0.050	0.050	0.050	0.050	0.050	Basic	-
L	0.025	0.025	0.025	0.030	0.030	0.030	0.030	±0.009	-
L1	0.041	0.041	0.041	0.056	0.056	0.056	0.056	Basic	-
h	0.013	0.013	0.013	0.020	0.020	0.020	0.020	Reference	-
Ν	8	14	16	16	20	24	28	Reference	-

Rev. M 2/07

#### NOTES:

- 1. Plastic or metal protrusions of 0.006" maximum per side are not included.
- 2. Plastic interlead protrusions of 0.010" maximum per side are not included.
- 3. Dimensions "D" and "E1" are measured at Datum Plane "H".
- 4. Dimensioning and tolerancing per ASME Y14.5M-1994



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